



Attorney's Docket No.. 07977-242001 / US3586

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Ohnuma, et al.                      Art Unit : 1765  
Serial No.: 09/050,182                      Examiner : R. Kunemund  
Filed : March 26, 1998                      Confirmation No. : 6531  
Title : METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE

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Commissioner for Patents  
Washington, D.C. 20231

AMENDMENT

Please amend the above-identified application as follows.

In the Claims:

Please amend the claims as follows.

1. (Amended) A method of manufacturing a semiconductor device including at least a thin film transistor, said method comprising the steps of:

E 1 forming an amorphous semiconductor film comprising silicon over a substrate having an insulating surface;

providing the amorphous semiconductor film with an element which promotes crystallization of the amorphous semiconductor film;

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, Washington, D.C. 20231.

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